

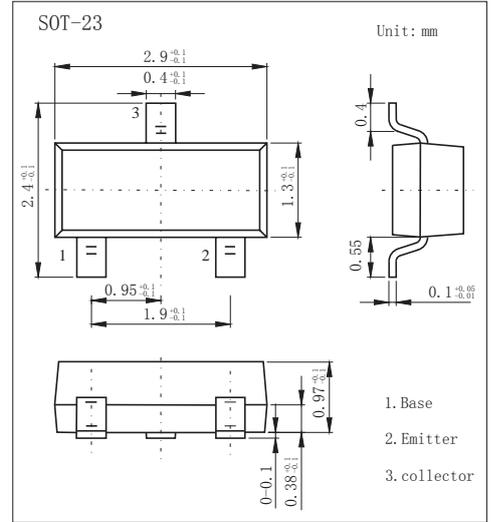
## SOT-23 Plastic-Encapsulate Transistors

### Features

- Epitaxial planar die construction.
- Complementary PNP type available (MMBT2907A)
- NPN General Purpose Amplifier

### MECHANICAL DATA

- Case style: SOT-23 molded plastic
- Mounting position: any



## MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V <sub>CB0</sub>	70	V
Collector - Emitter Voltage	V <sub>CEO</sub>	40	
Emitter - Base Voltage	V <sub>EBO</sub>	6	
Collector Current - Continuous	I <sub>c</sub>	600	mA
Power Dissipation	P <sub>D</sub>	250	mW
Thermal resistance from junction to ambient	R <sub>θJA</sub>	417	°C/W
Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature Range	T <sub>stg</sub>	-55 to 150	

### PACKAGE INFORMATION

Device	Package	Shipping
MMBT2222A (KMBT2222A)	SOT-23	3000/Tape&Reel

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	V <sub>(BR)CBO</sub>	I <sub>c</sub> = 100 μA, I <sub>E</sub> = 0	75			V
Collector-Emitter Breakdown Voltage	V <sub>(BR)CEO</sub>	I <sub>c</sub> = 10 mA, I <sub>B</sub> = 0	40			V
Emitter-Base Breakdown Voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> = 100 μA, I <sub>c</sub> = 0	6			V
Collector cutoff current	I <sub>CBO</sub>	V <sub>CB</sub> =60V, I <sub>E</sub> =0			100	nA
Collector cut-off current	I <sub>CEx</sub>	V <sub>CE</sub> =30V, V <sub>EB(off)</sub> =-3V			10	nA
Emitter cutoff current	I <sub>EBO</sub>	V <sub>EB</sub> = 3V, I <sub>c</sub> =0			100	nA
DC current gain	h <sub>FE</sub>	V <sub>CE</sub> =10V, I <sub>c</sub> = 0.1mA	40			
		V <sub>CE</sub> =10V, I <sub>c</sub> = 150mA	100		300	
		V <sub>CE</sub> =10V, I <sub>c</sub> = 500mA	42			
collector-emitter saturation voltage *	V <sub>CE(sat)</sub>	I <sub>c</sub> = 150 mA; I <sub>B</sub> = 15 mA			0.3	V
		I <sub>c</sub> = 500 mA; I <sub>B</sub> = 50 mA			1	V
base-emitter saturation voltage *	V <sub>BE(sat)</sub>	I <sub>c</sub> = 150 mA; I <sub>B</sub> = 15 mA	0.6		1.2	V
		I <sub>c</sub> = 500 mA; I <sub>B</sub> = 50 mA			2	V
Transition frequency	f <sub>T</sub>	I <sub>c</sub> = 20 mA; V <sub>CE</sub> = 20 V; f = 100 MHz	300			MHz
Delay time	t <sub>d</sub>	V <sub>CC</sub> =30V, V <sub>BE(off)</sub> =-0.5V,			10	ns
Rise time	t <sub>r</sub>	I <sub>c</sub> =150mA, I <sub>B1</sub> = 15mA			25	ns
Storage time	t <sub>s</sub>	V <sub>CC</sub> =30V, I <sub>c</sub> =150mA, I <sub>B1</sub> =-I <sub>B2</sub> =15mA			225	ns
Fall time	t <sub>f</sub>				60	ns

\* pulse test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2.0%.

### Marking

Marking	1P
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# RATINGS AND CHARACTERISTIC CURVES

## ■ Typical Characteristics

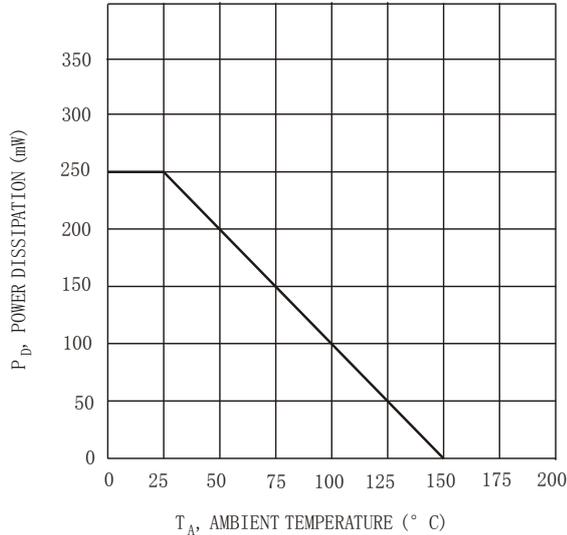


Fig. 1, Max Power Dissipation vs Ambient Temperature

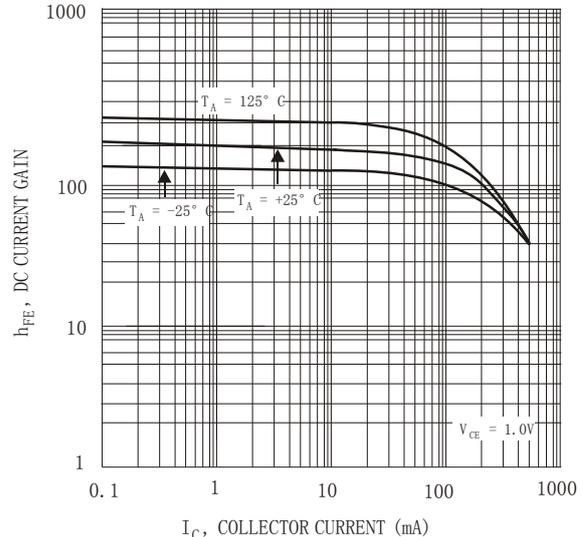


Fig. 2, Typical DC Current Gain vs Collector Current

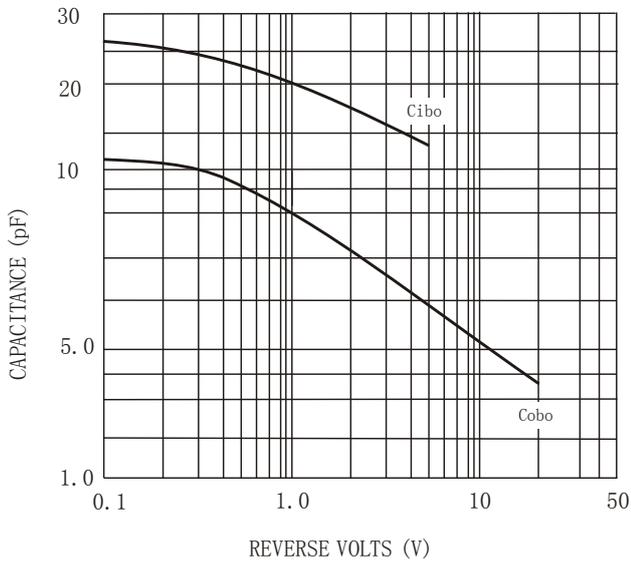


Fig. 3 Typical Capacitance

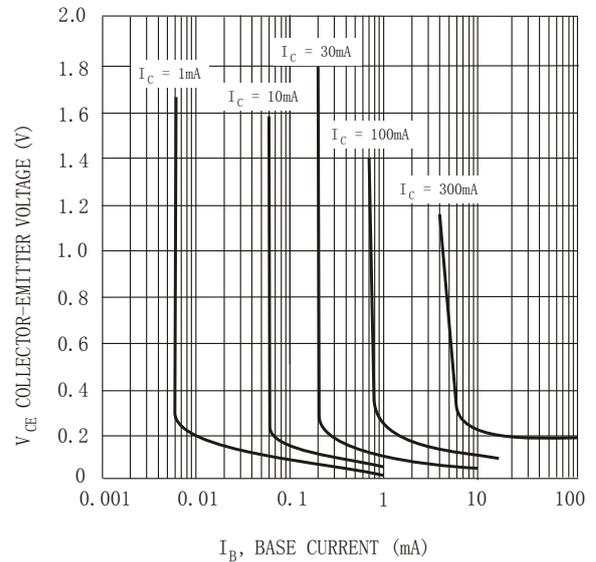


Fig. 4 Typical Collector Saturation Voltage